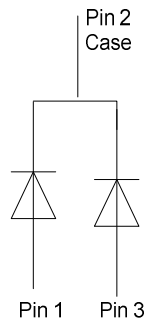
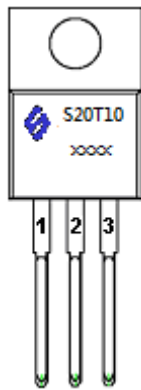


DESCRIPTION

STS20T10 is designed with trench technology to provide excellent low Vf. Those devices are suitable for use for switching power supply.

PIN CONFIGURATION (TO-220)



FEATURE

- ◆ $V_f \leq 0.65V$
- ◆ Fast Switching Speed
- ◆ Low Forward Voltage,
- ◆ Reliable High Temperature Operation
- ◆ Lead Free, RoHS Compliance

ORDERING INFORMATION

Part Number	Package	Part Marking
STS20T10T220RGB	TO-220	S20T10

※ STS20T10T220RGB: Tube; Pb – Free ; Halogen - Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Repetitive Peak Reverse Voltage	VRRM	100	V
DC Blocking Voltage	VRM	100	V
Working Repetitive Reverse Voltage	VRWM	100	V
Average Rectifier Forward Current per Leg	IO	10	A
Peak Forward Surge Current - 1/2 60Hz	IFSM	150	A
Repetitive Peak Reverse Surge Current	IRRM	1	A
Power dissipation	PD	165	W
Thermal Resistance Junction to Ambient	RθJC	2	°C/W
Storage Temperature Range	TSTG	-40 ~ 150	°C



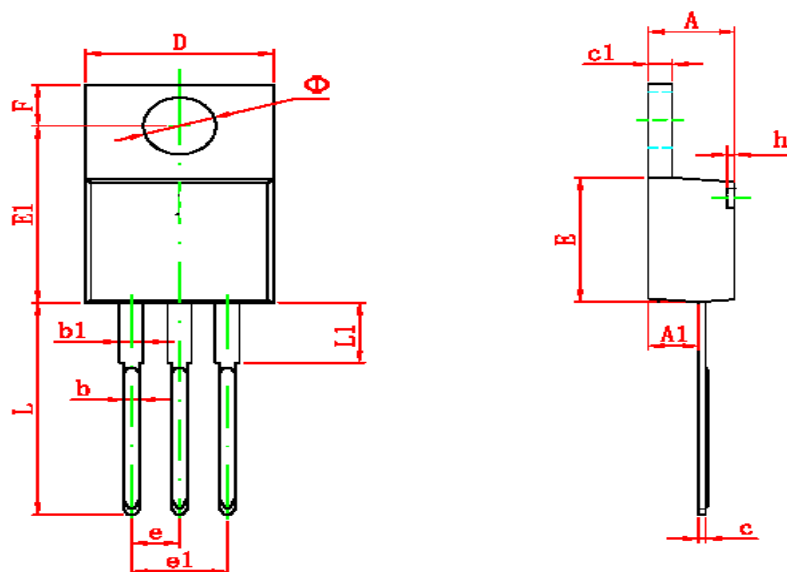
STS20T10
Low Vf Schottky Diode



20.0A

ELECTRICAL CHARACTERISTICS
(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Reverse Breakdown Voltage	VBR	IR = 10mA	100			V
Instantaneous Forward Voltage	VF	IF = 5A, TJ = 25°C		0.65		V
		IF = 10A, TJ = 25°C			0.75	
		IF = 5A, TJ = 125°C		0.5		
		IF = 10A, TJ = 125°C			0.65	
Instantaneous Reverse Current	IR	VR = 100V, TJ = 25°C			200	uA
		VR = 100V, TJ = 125°C			20	mA

TO-220 PACKAGE OUTLINE


Symbol	Millimeter		Inch	
	Min	Max	Min	Max
A	4.4	4.6	0.173	0.181
A1	2.23	2.53	0.088	0.100
b2	0.75	0.85	0.030	0.033
b1	1.17	1.42	0.046	0.056
c2	0.4	0.6	0.016	0.024
c1	1.2	1.4	0.047	0.055
D	9.85	10.15	0.388	0.400
E	8.96	9.46	0.353	0.372
E1	15.5	15.95	0.610	0.628
e	2.54REF		0.1REF	
e1	5.08REF		0.2REF	
F	2.7	2.9	0.106	0.114
h	0	0.3	0.000	0.012
L	12.7	13.65	0.500	0.537
L1		3.2		0.126